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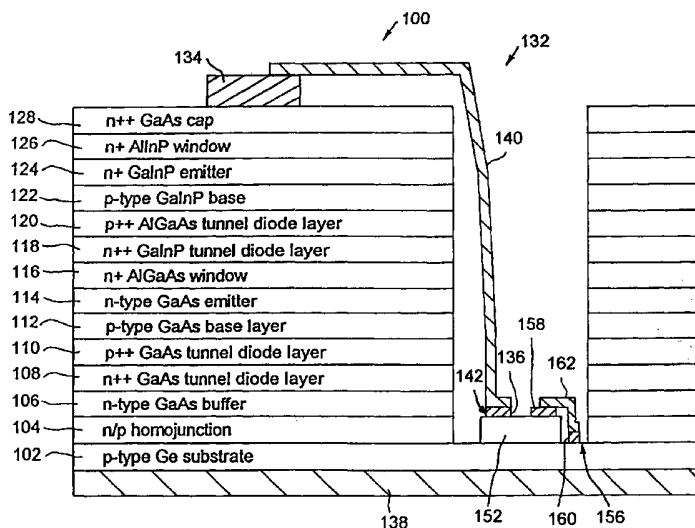
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(54) Title: SOLAR CELL HAVING A BYPASS DIODE FOR REVERSE BIAS PROTECTION AND METHOD OF FABRICATION



(57) Abstract: Reverse bias protection for a solar cell is provided with a diode on the solar cell. In one embodiment, the Schottky diode is formed at the interface between a metallic diode contact and a semiconductor substrate on which the solar cell is grown. The solar cell includes a Ge substrate, which may further include a photoactive junction. In one embodiment, the Schottky diode is provided in a trough or recess extending through the solar cell layers to the front surface of the substrate. In this embodiment, the Schottky diode is electrically connected across some or all of the cells of the solar cell structure with a jumper bar or other suitable interconnect. In another embodiment, the Schottky diode is provided on a back surface of the substrate, with a C-clamp interconnecting at least one solar cell contact to the diode contact.

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*For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.*



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C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

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Y	<p style="text-align: center;">---</p> US 6 252 287 B1 (ALLERMAN ANDREW A ET AL) 26 June 2001 (2001-06-26)  column 8, line 46 -column 9, line 64; figure 5	3-5, 11-13, 25, 46, 47, 50-52, 63, 65
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